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T-453 P.012/022

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DATE: March 26, 2004  
FILE NO.: AMAT/1831.P1/CPI/COPPER/PJS  
TO: Examiner: Ginette Peralta  
FAX NO.: 703-872-8308  
COMPANY: USPTO  
FROM: Keith M. Tadbett  
PAGE(S) with cover: 7  
ORIGINAL TO FOLLOW?  YES  NO

TITLE: Reliability Barrier Integration for CU Application  
U.S. SERIAL NO.: 10/052,681  
FILING DATE: January 17, 2002  
INVENTOR: XI, et al.  
EXAMINER: Ginette Peralta  
GROUP ART UNIT: 2814  
CONFIRMATION NO.: 4083

RULE 312 AMENDMENT AFTER ALLOWANCE

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PAGE 12/22 \* RCV'D AT 2/2/2005 6:44:14 PM [Eastern Standard Time] \* SVR:USPTO-EFXRF-1/3 \* DNIS:8729306 \* CSID:+7136234846 \* DURATION (mm:ss):05:12

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:  
Xi, et al.§  
§ Group Art Unit: 2814

Serial No.: 10/052,681

§  
§ Examiner: Ginette Peralta

Confirmation No.: 4083

§  
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Filed: January 17, 2002

For: Reliability Barrier Integration for  
CU ApplicationMAIL STOP ISSUE FEE  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**CERTIFICATE OF FACSIMILE  
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I hereby certify that this correspondence and the documents referred to as attached thereto are being facsimile transmitted to the U.S. Patent and Trademark Office to the fax number indicated by the Examiner, namely, fax number (703) 872-9306 to the attention of the named Examiner, on the date below.

<u>3/14/04</u>	<u>Karen M. Zaleski</u>
Date	Signature

## RULE 312 AMENDMENT AFTER ALLOWANCE

Following mailing of a Notice of Allowance on December 31, 2003, Applicants request entry of the following amendment to correct the dependency of an allowed claim. **Amendments to the Claims** are shown in the listing of the claims beginning on page 2 of this paper. **Remarks** begin on page 8 of this paper.

**COPY****IN THE CLAIMS:**

Please amend the claims as follows:

1. (Previously Presented) A method of filling one or more of a via and a trench in a patterned substrate, comprising:
  - a) depositing a generally conformal first barrier layer in one or more of the via and the trench on the patterned substrate by chemical vapor deposition, wherein the first barrier layer is selected from the group consisting of TiSi<sub>x</sub>N, TiN(C), TiNSi(C), Ta, TaC, TaN(C), TaNSi(C), W, WN<sub>x</sub>, SiO<sub>x</sub>N<sub>y</sub>, SiC, AlN, and Al<sub>2</sub>O<sub>3</sub>;
  - b) removing the first barrier layer from the horizontal surfaces of the patterned substrate;
  - c) depositing a second barrier layer by physical vapor deposition; and then
  - d) depositing one or more conductive materials.
2. (Original) The method of claim 1 wherein depositing the conductive material comprises depositing a seed layer and a metal layer in the via and/or the trench after the second barrier layer is deposited.
3. (Previously Presented) The method of claim 2 wherein the first barrier layer is selected from the group consisting of TiN(C), Ta, TaC, TaN(C), W, WN<sub>x</sub>, SiC, AlN, and Al<sub>2</sub>O<sub>3</sub>.
4. (Previously Presented) The method of claim 1 wherein the second barrier layer is selected from the group consisting of Ta, TaN, TiSiN<sub>x</sub>, TaSiN<sub>x</sub>, W, and WN<sub>x</sub>.
5. (Currently Amended) The method of claim [4] 2 wherein the seed layer is copper.
6. (Original) The method of claim 5 wherein the metal layer is copper.

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7. (Original) The method of claim 1 wherein the first barrier layer is deposited and removed from the horizontal surfaces of the patterned substrate within a single chamber of an integrated processing tool.
8. (Original) The method of claim 7 wherein the chamber is a chemical vapor deposition chamber and the first barrier layer is deposited and etched in the chamber.
9. (Original) The method of claim 2 wherein the seed layer is deposited by physical vapor deposition.
10. (Original) The method of claim 2 wherein the seed layer is deposited by chemical vapor deposition.
11. (Original) The method of claim 2 wherein the seed layer is deposited by electroless deposition.
12. (Original) The method of claim 2 wherein the metal layer is deposited by physical vapor deposition.
13. (Original) The method of claim 2 wherein the metal layer is deposited by chemical vapor deposition.
14. (Original) The method of claim 2 wherein the metal layer is deposited by electroplating.
15. (Original) The method of claim 1 wherein the via has an aspect ratio of about 4 to 1 and the trench has an aspect ratio of about 1 to 1.
16. (Original) The method of claim 1 wherein the second barrier layer has a thickness of from about 20 Å to about 50 Å at the bottom of the via.

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17. (Original) The method of claim 1 wherein the second barrier layer is selected from the group consisting of Ta, TaN, W, WN<sub>x</sub>, Ti, and TiN, and the second barrier layer has a thickness of from about 20 Å to about 50 Å at the bottom of the via.

18. (Original) A method of filling one or more of a via and a trench in a patterned substrate, comprising:

- a) depositing a generally conformal first barrier layer on the patterned substrate by atomic layer deposition;
- b) removing the first barrier layer from the horizontal surfaces of the patterned substrate;
- c) depositing a second barrier layer by physical vapor deposition; and then
- d) depositing one or more conductive materials.

19. (Original) The method of claim 18 wherein depositing the conductive material comprises depositing a seed layer and a metal layer in the via and/or the trench after the second barrier layer is deposited.

20. (Original) The method of claim 19 wherein the first barrier layer is selected from the group consisting of Ta, TaN, W, and WN.

21. (Original) The method of claim 20 wherein the second barrier layer is selected from the group consisting of Ta, TaN, TiSiN<sub>x</sub>, TaSiN<sub>x</sub>, W, and WN<sub>x</sub>.

22. (Original) The method of claim 21 wherein the seed layer is copper.

23. (Original) The method of claim 22 wherein the metal layer is copper.

24. (Original) The method of claim 18 wherein the first barrier layer is deposited and removed from the horizontal surfaces of the patterned substrate within a single chamber of an integrated processing tool.

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25. (Original) The method of claim 24 wherein the chamber is an atomic layer deposition chamber and the first barrier layer is deposited and etched in the chamber.

26. (Original) The method of claim 19 wherein the seed layer is deposited by physical vapor deposition.

27. (Original) The method of claim 19 wherein the seed layer is deposited by chemical vapor deposition.

28. (Original) The method of claim 19 wherein the seed layer is deposited by electroless deposition.

29. (Original) The method of claim 19 wherein the metal layer is deposited by physical vapor deposition.

30. (Original) The method of claim 19 wherein the metal layer is deposited by chemical vapor deposition.

31. (Original) The method of claim 19 wherein the metal layer is deposited by electroplating.

32. (Original) The method of claim 18 wherein the via has an aspect ratio of about 4 to 1 and the trench has an aspect ratio of from about 1 to about 1.

33. (Original) The method of claim 18 wherein the second barrier layer has a thickness of from about 20 Å to about 50 Å at the bottom of the via.

34. (Original) The method of claim 18 wherein the second barrier layer is selected from the group consisting of Ta, TaN, W, WN<sub>x</sub>, Ti, and TiN, and the second barrier layer has a thickness of from about 20 Å to about 50 Å at the bottom of the via.

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35. (Original) A method of filling one or more of a via and a trench in a patterned substrate having an etch stop at the via level, comprising:

- a) depositing a generally conformal first barrier layer on the patterned substrate by chemical vapor deposition;
- b) removing the first barrier layer from the horizontal surfaces of the patterned substrate;
- c) removing the etch stop from the bottom of the via;
- d) depositing a second barrier layer by physical vapor deposition; and then
- e) depositing one or more conductive materials.

36. (Original) The method of claim 35 wherein depositing the conductive material comprises depositing a seed layer and a metal layer in the via and/or the trench after the second barrier layer is deposited.

37. (Previously Presented) A method of filling one or more of a via and a trench in a patterned substrate having a metal layer underlying the via, comprising:

- a) depositing a generally conformal first barrier layer on the patterned substrate by chemical vapor deposition, wherein the first barrier layer is selected from the group consisting of TiSi<sub>x</sub>N, TiN(C), TiNSi(C), Ta, TaC, TaN(C), TaNSi(C), W, WN<sub>x</sub>, SiO<sub>x</sub>N<sub>y</sub>, SiC, AlN, and Al<sub>2</sub>O<sub>3</sub>;
- b) removing the first barrier layer from the horizontal surfaces of the patterned substrate;
- c) depositing by physical vapor deposition a second barrier layer sufficient to provide a barrier on the bottom of the trench without significantly impairing conduction between the conductive material deposited in the via and the metal layer ; and then
- d) depositing one or more conductive materials.

38. (Original) A method of filling one or more of a via and a trench in a patterned substrate having a metal layer underlying the via, comprising:

- a) depositing a generally conformal first barrier layer on the patterned substrate by atomic layer deposition;

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- b) removing the first barrier layer from the horizontal surfaces of the patterned substrate;
- c) depositing by physical vapor deposition a second barrier layer sufficient to provide a barrier on the bottom of the trench without significantly impairing conduction between the conductive material deposited in the via and the metal layer ; and then
- d) depositing one or more conductive materials.

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**REMARKS**

This amendment is filed to correct the dependency of claim 5 to provide antecedent basis for the phrase "seed layer" in claim 5. Applicants believe that no new matter has been introduced in this response. Entry of the amendment is respectfully requested.

Respectfully submitted,



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**DATE:** March 4, 2004  
**FILE NO.:** 7MAT/1931-P1/CPI/COPPER/PJS  
**TO:** Examiner: Ginette Peralta  
**FAX NO.:** 103-872-6306  
**COMPANY:** USPTO  
**FROM:** Keith M. Tackett  
**PAGE(S) with cover:** 21  
**ORIGINAL TO FOLLOW?**  YES  NO

**RULE 312 AMENDMENT AFTER ALLOWANCE**

**TITLE:** Reliability Barrier Integration for GU Application  
**U.S. SERIAL NO.:** 10/62,681  
**FILING DATE:** January 17, 2002  
**INVENTOR:** et al.  
**EXAMINER:** Ginette Peralta  
**GROUP ART UNIT:** 2814  
**CONFIRMATION NO.:** 1083

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RULE 312 AMENDMENT AFTER ALLOWANCE						
TITLE:	100% Java(tm) Barrier Integration for GUI Applications					
U.S. SERIAL NO.:	10/62,691					
FILING DATE:	January 17, 2002					
INVENTOR:	;d, et al.					
EXAMINER:	Cinetra Peralta					
GROUP ART UNIT:	2814					
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FAX NO: 703-872-9306  
COMPANY: USPTO  
FROM: Keith M. Tackett  
PAGE(S) with cover: 22  
ORIGINAL TO FOLLOW?  YES  NO

### SUBMISSION OF REPLACEMENT DOCUMENTS

TITLE: Reliability Barrier Integration for CU Application  
U.S. SERIAL NO.: 10/052,681  
FILING DATE: January 17, 2002  
INVENTOR: Xi, et al.  
EXAMINER: Ginette Peralta  
GROUP ART UNIT: 2814  
CONFIRMATION NO.: 4083

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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of:  
Xi, et al.

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Serial No.: 10/052,681

Group Art Unit: 2814

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Confirmation No.: 4083

Examiner: Ginette Peralta

Filed: January 17, 2002

For: Reliability Barrier Integration CU  
Application

Commissioner for Patents  
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Alexandria, VA 22313-1450

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<u>2/2/05</u>	<u>Karen Mbs</u>
Date	Signature

Dear Sir:

**SUBMISSION OF REPLACEMENT DOCUMENTS**

Applicants note that while the issue fee for the instant application was paid on March 31, 2004, the instant application has not yet issued. The Examiner indicated in a telephone conversation on February 1, 2005 that the issue fee payment and the amendments after allowance filed on March 4, 2004 and March 26, 2004 have been received by the Patent Office, but have not been matched with the file.

Applicants are submitting a copy of the issue fee transmittal and the return receipt postcard indicating that the issue fee transmittal was received by the Patent Office on April 5, 2004. Applicants are also submitting a copy of the amendment after allowance filed March 4, 2004, with its facsimile confirmation and a copy of the amendment after allowance filed March 26, 2004, with its facsimile confirmation.

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T-453 P.003/022 F507

PATENT

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Applicants are submitting the attached copies to replace the misplaced issue fee transmittal and amendments after allowance to help expedite the issuance of the patent for the instant application.

Respectfully submitted,



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APPLICATION  
Inventor Ming XIA et al  
Serial No 10/052,681 Filed 01/17/2002  
Atty Dkt No 001931 P 01 USA/CPI/COPPER

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